



PTO-1449 (MPEP 609) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT	ATTY. DOCKET NO. 211.001-D3-US	SERIAL NUMBER 10/724,648
	APPLICANT(S) Fazan et al.	
	FILING DATE December 1, 2003	GROUP ART UNIT

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WSL	4,032,947	6/1977	Kesel et al.			
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	5,448,513	9/1995	Hu et al.			
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	3,439,214	4/1969	Kabell			
	6,081,443	6/2000	Morishita			
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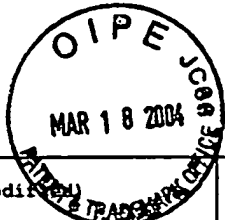
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WSL	FR 2 197 494	3/1974	French			
	EP 1 180 799	2/2002	European			
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	GB 1 414 228	11/1975	Great Britain			
	EP 0 694 977	1/1996	European			
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	EP 1 237 193	9/2002	European			
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WSL	"The Multistable Charge-Controlled Memory Effect in SOI MOS Transistors at Low Temperatures", Tack et al., IEEE Transactions on Electron Devices, Vol. 37, No. 5, May 1990, pp.1373-1382

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WSL	EP 0 801 427	10/1997	European			
WSL	EP 0 513 923	11/1992	European			

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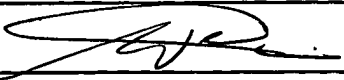
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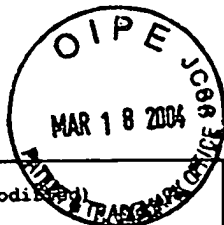
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EXAMINER <i>Stefan</i>	DATE CONSIDERED <i>1/5/05</i>
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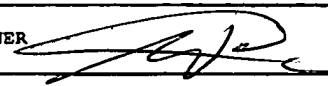
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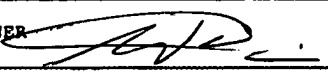
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WSL	5,886,385	3/1999	Arisumi et al.			
WSL	5,929,479	7/1999	Oyama			

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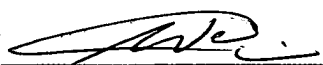
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WSL	6,391,658	5/2002	Gates et al.			

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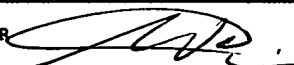
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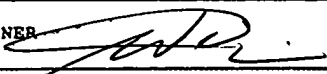
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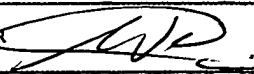
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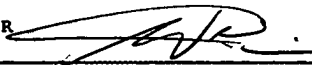
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WSL	EP 0 951 072 A1	10/1999	European			
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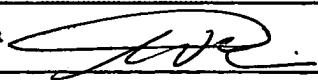
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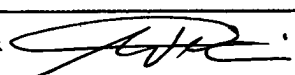
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WSL	6,297,090	10/2001	Kim			
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WSL	JP 62 272561	11/1987	Japanese			
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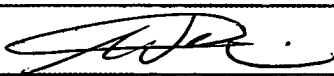
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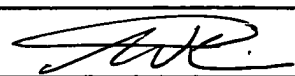
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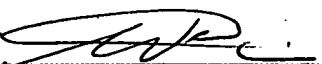
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